

SE60120B

N-Channel Enhancement-Mode MOSFET

Revision: A

General Description

This type used advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge.

- High density cell design for ultra low $R_{DS(ON)}$
- Excellent package for good heat dissipation

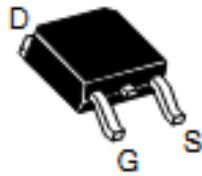
Features

For a single MOSFET

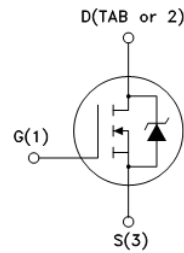
- $V_{DS} = 60V$
- $R_{DS(ON)} = 4.1m\Omega @ V_{GS}=10V$

Pin configurations

See Diagram below



TO-252



Absolute Maximum Ratings

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	Continuous	I_D	120	A
	Pulsed		420	
Total Power Dissipation	@TA=25°C	P_D	200	W
Operating Junction Temperature Range		T_J	-55 to 175	°C

SE60120B

Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0 V	60			V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 60V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	2		4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =40A		4.1	5.5	mΩ
g _{FS}	Forward Transconductance	V _{DS} =25V, I _D =40A	50			S
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, f=1MHz		4900		pF
C _{oss}	Output Capacitance			470		pF
C _{rss}	Reverse Transfer Capacitance			460		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge ²	V _{GS} =10V, V _{DS} =30V, I _D =30A		125		nC
Q _{gs}	Gate Source Charge			24		nC
Q _{gd}	Gate Drain Charge			49		nC
t _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =30V, R _{GEN} =2.5Ω		20		ns
t _{d(off)}	Turn-Off Delay Time			70		ns
t _{d(r)}	Turn-On Rise Time			19		ns
t _{d(f)}	Turn-Off Fall Time			30		ns
Thermal Resistance						
Symbol	Parameter	Min	Typ	Units		
R _{θJC}	Junction to Case	0.35	0.55	°C/W		

Typical Characteristics

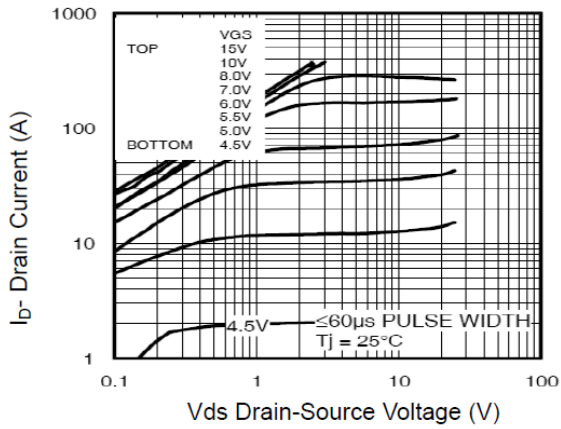


Figure 1 Output Characteristics

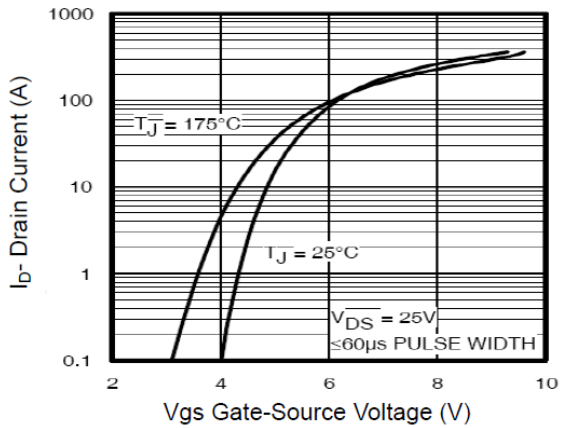


Figure 2 Transfer Characteristics

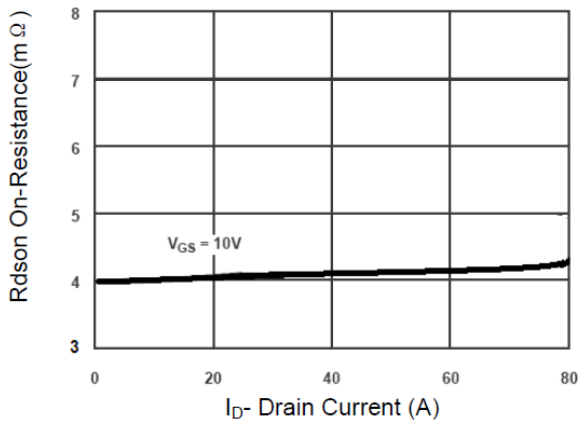


Figure 3 Rdson- Drain Current

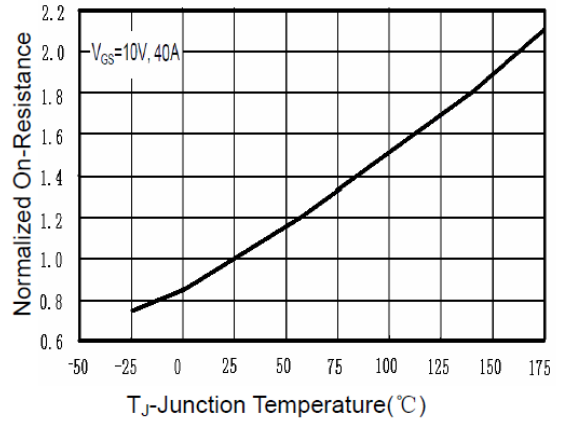


Figure 4 Rdson-Junction Temperature

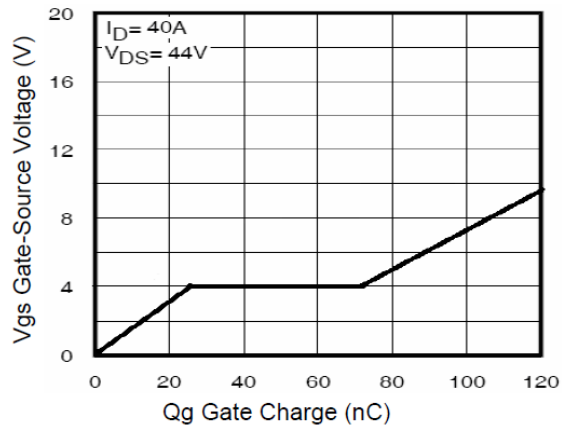


Figure 5 Gate Charge

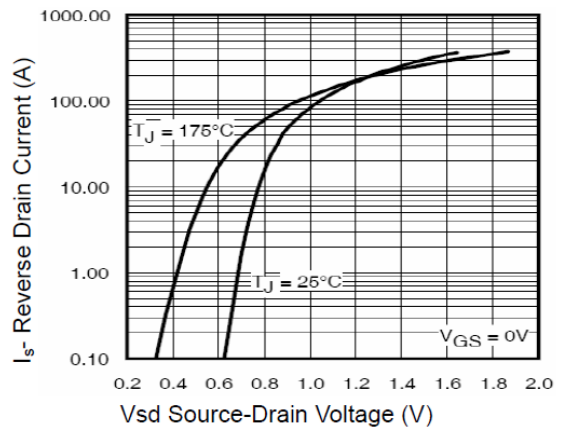


Figure 6 Source- Drain Diode Forward

Typical Characteristics

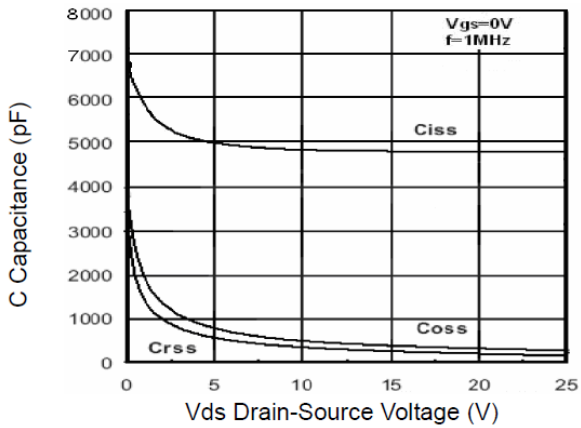


Figure 7 Capacitance vs Vds

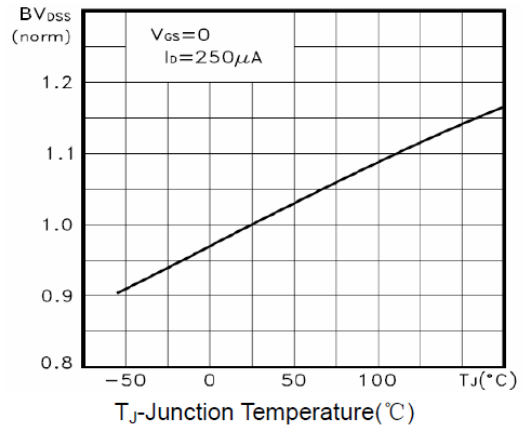


Figure 9 BV_{DSS} vs Junction Temperature

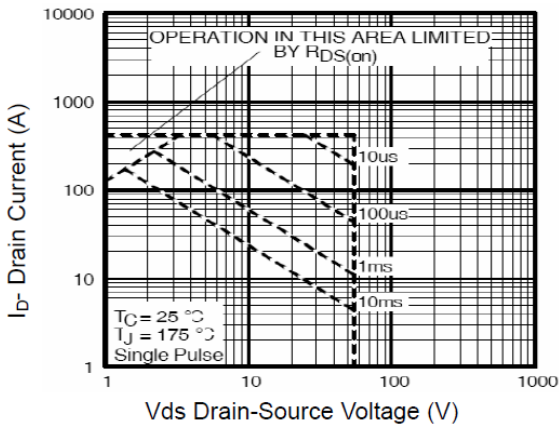


Figure 8 Safe Operation Area

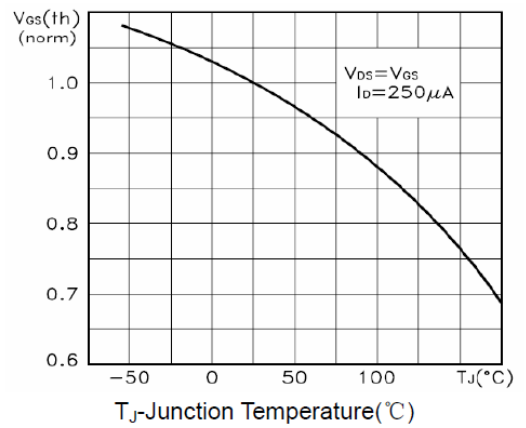


Figure 10 $V_{GS(th)}$ vs Junction Temperature

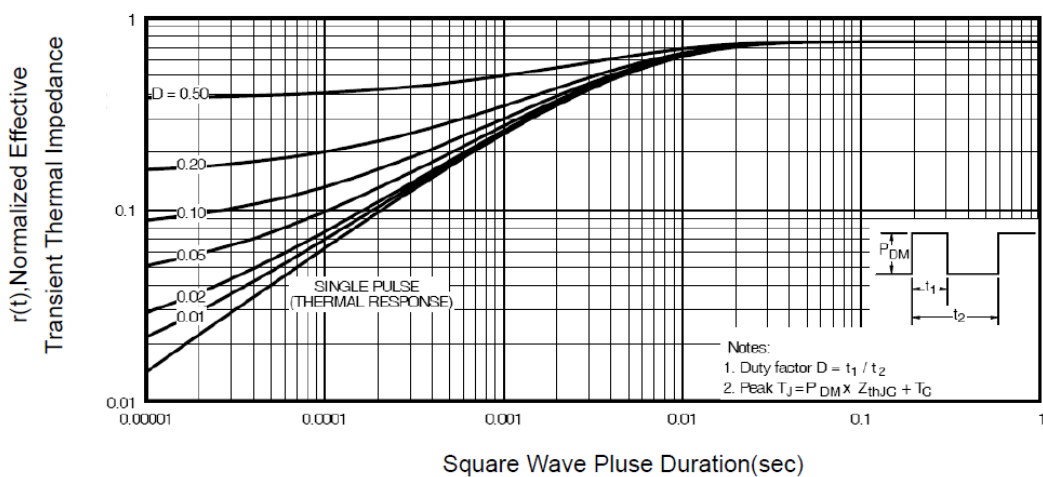
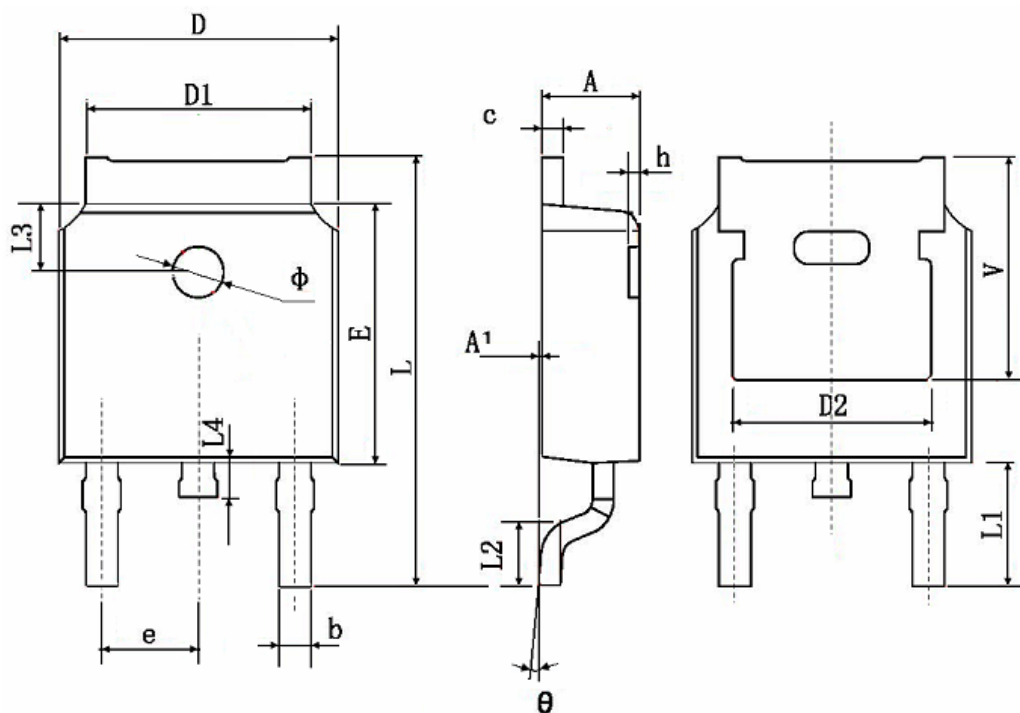


Figure 11 Normalized Maximum Transient Thermal Impedance

SE60120B

Package Outline Dimension

TO-252



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
ϕ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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